

P-Ch 20V Fast Switching MOSFETs

- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent Cdv/dt effect decline
- ★ Advanced high cell density Trench technology

Product Summary

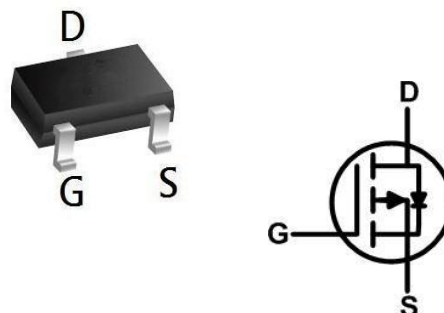


BVDSS	RDS(on)	ID
-20V	20mΩ	-7.0A

Description

The UD20P07L is the high cell density trench P-ch MOSFETs, which provides excellent RDS(on) and efficiency for most of the small power switching and load switch applications. The UD20P07L meets the RoHS and Green Product requirement with full function reliability approved.

SOT23-3L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	-20	V
V _{GS}	Gate-Source Voltage	±12	V
I _D @T _A =25°C	Continuous Drain Current, V _{GS} @ -4.5V ¹	-7.0	A
I _D @T _A =70°C	Continuous Drain Current, V _{GS} @ -4.5V ¹	-4.8	A
I _{DM}	Pulsed Drain Current ²	-18.8	A
P _D @T _A =25°C	Total Power Dissipation ³	1.5	W
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction-ambient ¹	---	115	°C/W
R _{θJC}	Thermal Resistance Junction-Case ¹	---	80	°C/W

Electrical Characteristics (T_J=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D = -250μA	-20	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -20V, V _{GS} =0V,	-	-	-1	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} = ±12V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D = -250μA	-0.4	-0.7	-1.0	V
R _{DS(on)}	Static Drain-Source on-Resistance note2	V _{GS} = -4.5V, I _D = -5A	-	20	26	mΩ
		V _{GS} = -2.5V, I _D = -4A	-	27	37	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = -10V, V _{GS} =0V, f=1.0MHz	-	1200	-	pF
C _{oss}	Output Capacitance		-	191	-	pF
C _{rss}	Reverse Transfer Capacitance		-	168	-	pF
Q _g	Total Gate Charge	V _{DS} = -10V, I _D = -5A, V _{GS} = -4.5V	-	33.7	-	nC
Q _{gs}	Gate-Source Charge		-	3.5	-	nC
Q _{gd}	Gate-Drain(“Miller”) Charge		-	10.5	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DD} = -10V, I _D = -5A, V _{GS} = -4.5V,R _{GEN} =10Ω	-	11	-	ns
t _r	Turn-on Rise Time		-	35	-	ns
t _{d(off)}	Turn-off Delay Time		-	30	-	ns
t _f	Turn-off Fall Time		-	10	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	-5	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-20	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _S = -5A	-	-	-1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%

Typical Performance Characteristics

Figure 1: Output Characteristics

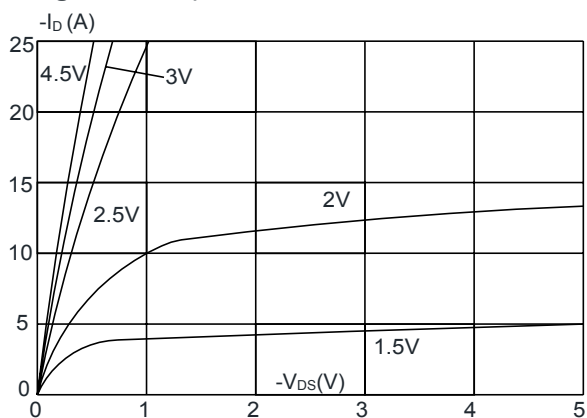


Figure 2: Typical Transfer Characteristics

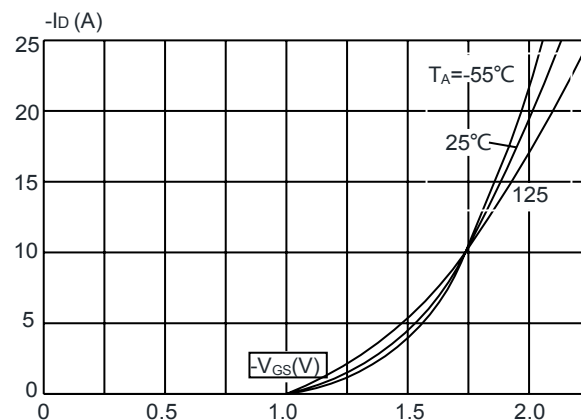


Figure 3: On-resistance vs. Drain Current

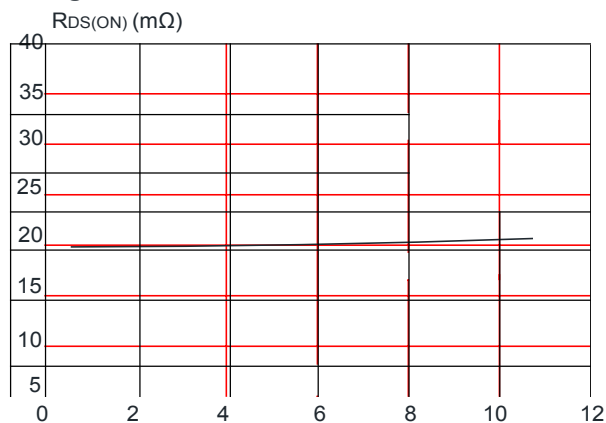


Figure 4: Body Diode Characteristics

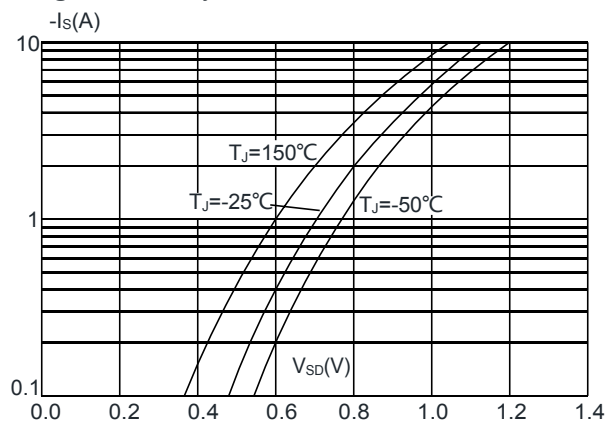


Figure 5: Gate Charge Characteristics

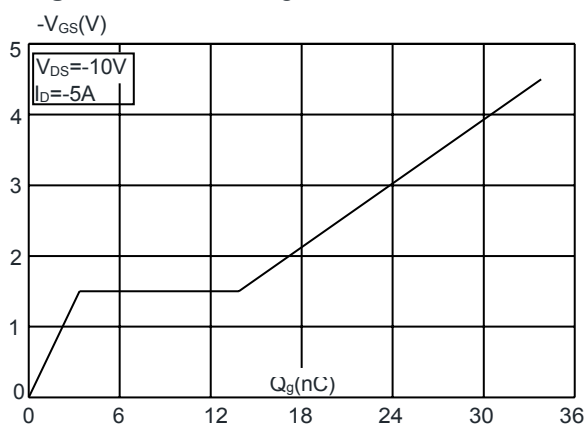
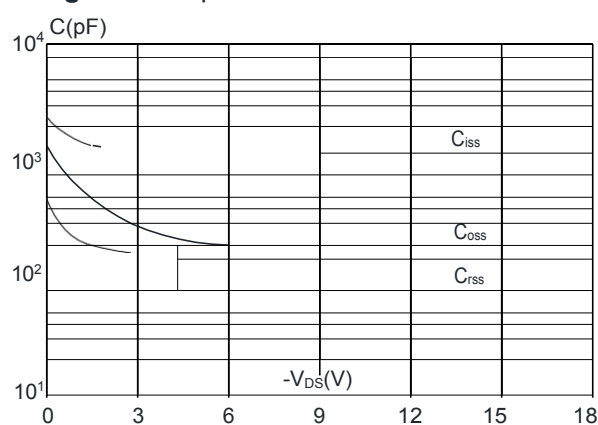


Figure 6: Capacitance Characteristics



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Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

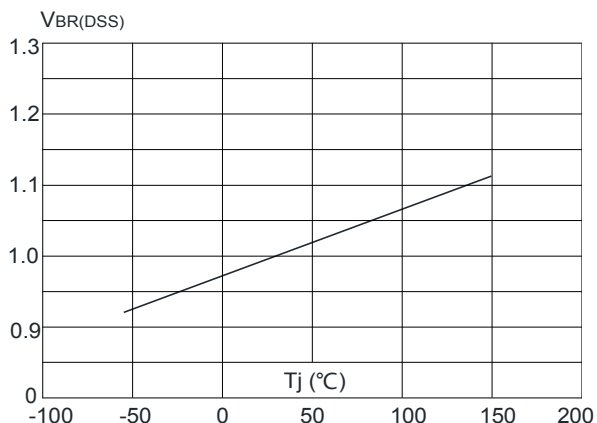


Figure 8: Normalized on Resistance vs. Junction Temperature

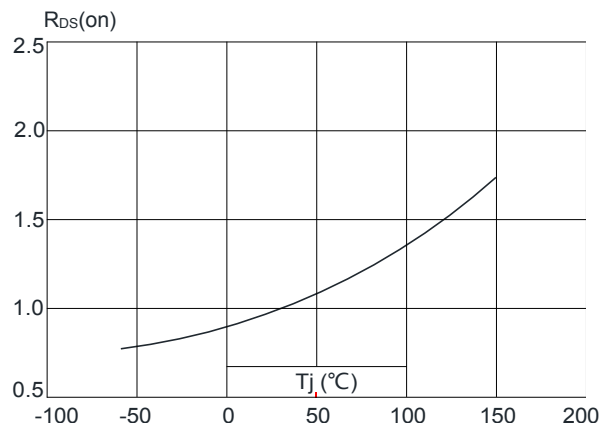


Figure 9: Maximum Safe Operating Area

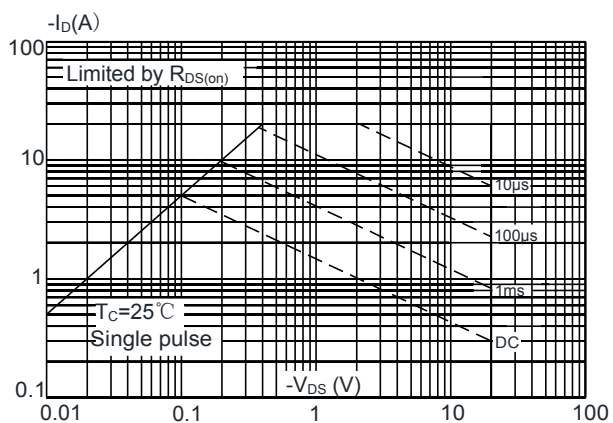


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

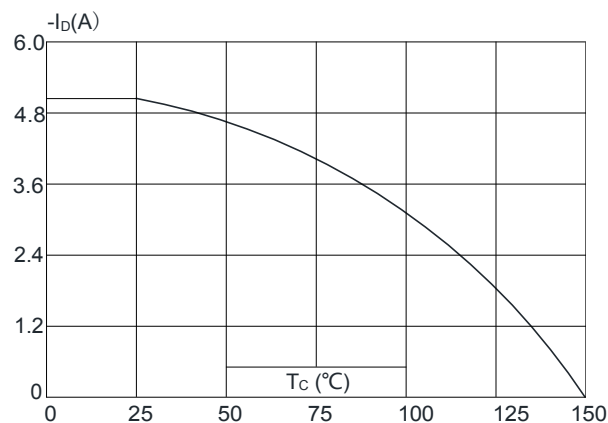
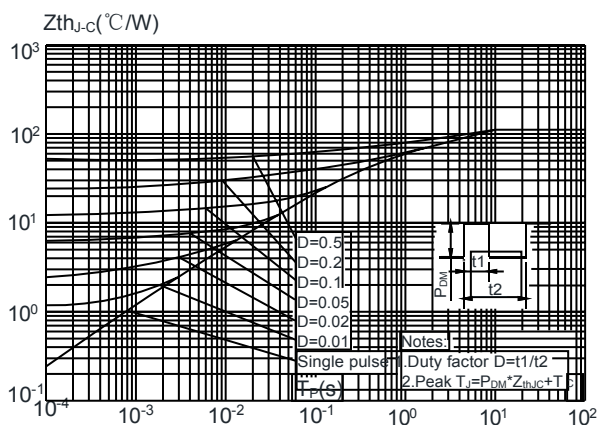
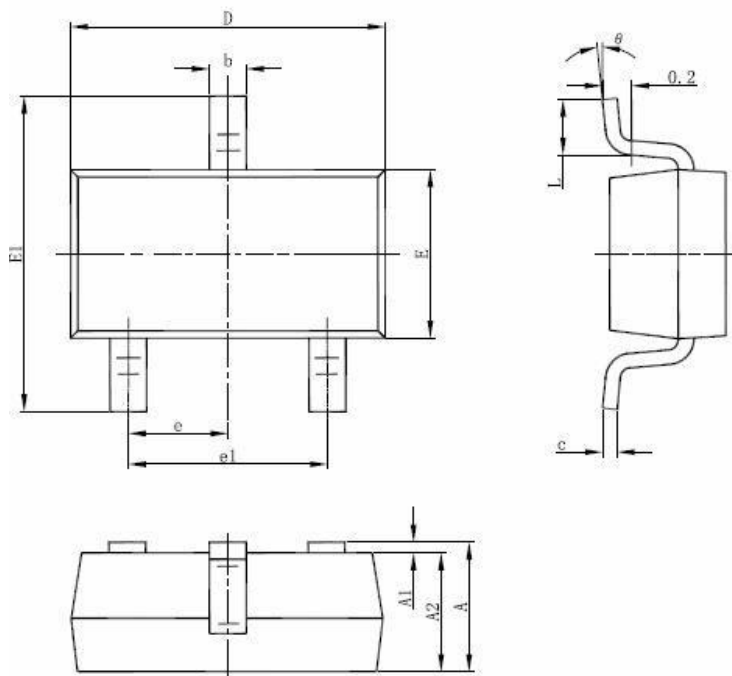


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case



SOT-23-3L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°